

SPEC No.	CC057003B
ISSUE: Nov 18 1993	

To: _____

PRELIMINARY SPECIFICATIONS

Product Type 1/3 type solid state color imaging device for NTSC system

Model No. LZ2313H5
(LZ2313H5)

※This specifications contains 18 pages including the cover and appendix.
If you have any objections, please contact us before issuing purchasing order.

CUSTOMERS ACCEPTANCE

DATE: _____

BY: _____

PRESENTED

BY: K. Misawa
K. MISAWA
Dept. General Manager

REVIEWED BY:

PREPARED BY:

Development Dept. 4
VLSI Laboratories
Integrated Circuits Group
SHARP CORPORATION

I. Fubz

3. PIN ASSIGNMENT AND PIN IDENTIFICATION

GND	$\phi V4$	$\phi V3$	$\phi V2$	$\phi V1$	PW	OFD	T1
16	15	14	13	12	11	10	9
LZ2313H5 ▽							
1	2	3	4	5	6	7	8
OD	ϕRS	RD	OS	NC1	NC2	$\phi H2$	$\phi H1$

Symbol	Pin name
RD	Reset transistor drain
OD	Output transistor drain
OS	Video output
ϕRS	Reset transistor gate clock
$\phi V1, \phi V2, \phi V3, \phi V4$	Vertical shift register gate clock
$\phi H1, \phi H2$	Horizontal shift register gate clock
OFD	Overflow drain
PW	P type well
GND	Ground
T1	Test terminals
NC1, NC2	Non-connection (note 1)

(note 1) Connect each pin to GND directly or through a capacitor larger than $0.047\mu F$.

4. ABSOLUTE MAXIMUM RATING

(Ta = 25°C)

Item	Symbol	Rating	Unit
Output transistor drain voltage	VOD	0 to +18	V
Reset transistor drain voltage	VRD	0 to +18	V
Overflow drain voltage	VOFD	0 to +55	V
Test terminal, T1	VT1	0 to +18	V
Reset gate clock voltage	V ϕRS	-0.3 to +18	V
Vertical shift register clock voltage	V ϕV	-9.0 to +18	V
Horizontal shift register clock voltage	V ϕH	-0.3 to +18	V
PW and vertical clock voltage difference	VPW-V ϕV	-27 to 0	V
Storage temperature	Tstg	-40 to +80	°C
Operating ambient temperature	Topr	-20 to +70	°C

5. RECOMMENDED OPERATING CONDITIONS

Item		Symbol	Minimum	Typical	Maximum	Unit
Operating ambient temperature		T _{opr}		25.0		°C
Output transistor drain voltage		V _{OD}	14.5	15.0	16.0	V
Reset transistor drain voltage		V _{RD}		V _{OD}		V
Overflow drain voltage	When DC is applied(note1)	V _{OFD}	5.0	(adj.)	19.0	V
	When pulse is applied p-p level (note2)	V _{φOFD}	22.0			V
Ground		G _{ND}		0.0		V
P-well voltage		V _{PW}	-9.0		V _{φVL}	V
Test terminal, T1		V _{T1}		V _{OD}		V
Vertical shift register clock	LOW level	V _{φV1L} , V _{φV2L} V _{φV3L} , V _{φV4L}	-8.5	-8.0	-7.5	V
	INTERMEDIATE level	V _{φV1I} , V _{φV2I} V _{φV3I} , V _{φV4I}		0.0		V
	HIGH level	V _{φV1H} , V _{φV3H}	16.0	16.5	17.0	V
Horizontal shift register clock	LOW level	V _{φH1L} , V _{φH2L}	-0.05	0.0	0.05	V
	HIGH level	V _{φH1H} , V _{φH2H}	4.7	5.0	6.0	V
Reset gate clock	LOW level	V _{φRSL}	0.0		V _{RD} -13.0	V
	HIGH level	V _{φRSH}	V _{RD} -8.5		9.5	V
Frequency						
Vertical shift register clock		f _{φV1} , f _{φV2} f _{φV3} , f _{φV4}		15.73		k Hz
Horizontal shift register clock		f _{φH1} , f _{φH2}		9.53		M Hz
Reset gate clock		f _{φRS}		9.53		M Hz

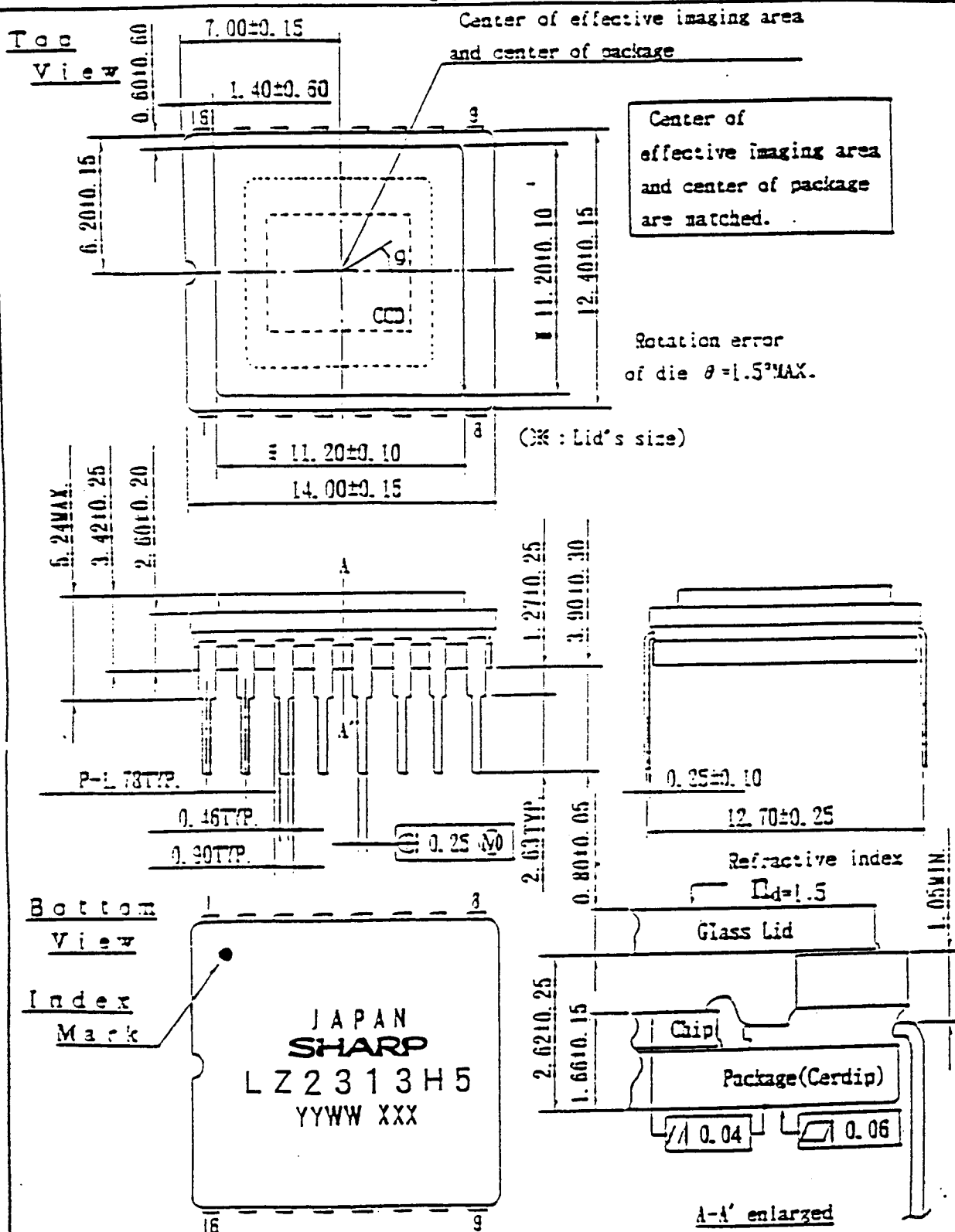
(note1) When DC voltage is applied, shutter speed is 1/60 seconds.

(note2) When pulse is applied, shutter speed is less than 1/60 seconds.

6. CHARACTERISTICS

No.	Item	Symbol	Note	Min.	Typ.	Max.	Unit
1	Photo response non-uniformity	PRNU	(a)			15	%
2	Carrier saturation	V _{sat}	(b)	450			m V
3	Dark output voltage	V _{dark}	(c)		0.3	3.0	m V
4	Dark signal non-uniformity	DSNU	(d)		0.6	2.0	m V
5	Sensitivity	R	(e)	440	600		m V
6	Smear ratio	SMR	(f)		0.009	0.016	%
7	Image lag	AI	(g)			1.0	%
8	Blooming suppression ratio	ABL	(h)	100			
9	Current dissipation	I _{oo}			4.0	8.0	m A
10	Output impedance	R _o			350		Ω
11	Vector breakup		(i)			5.0	°, %
12	Line crawling		(j)			3.0	%
13	Luminance flicker		(k)			2.0	%

LZ2313H5



(Unit : mm)

ITEM MATERIAL	ITEM	FINISH	% R	NAME
				DMPG16C
			7-5	
			CODE	
4-74 423571	IC GROUP			
(VLSI) DEVELOPMENT DEPT.5	14	6		00001600000000

CCD sensor imaging area sensor pattern recognition LZ2 timing generator vertical driver white balance